

isc Silicon NPN Pow Transistor

2SC2229

DESCRIPTION

- High breakdown voltage
- Low output capacitance
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

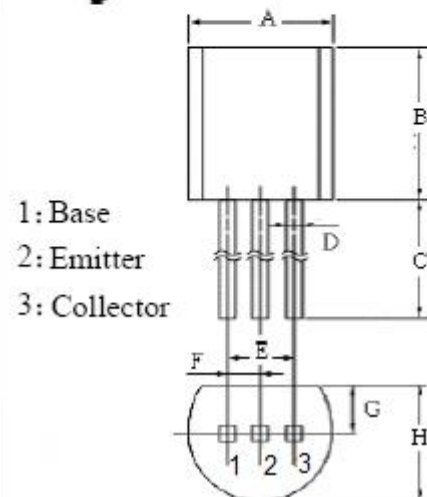
APPLICATIONS

- High voltage switching applications
- Driver stage audio amplifier applications
- Black and white TV video output applications

ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	200	V
V_{CEO}	Collector-Emitter Voltage	1500	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current-Continuous	50	mA
I_E	Emitter Current-Continuous	-50	mA
P_C	Collector Power Dissipation @ $T_c=25^\circ\text{C}$	0.8	W
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature Range	-55~150	$^\circ\text{C}$

TO-92 package



DIM	mm	
	MIN	MAX
A	4.33	4.83
B	4.33	4.83
C	14.0	15.0
D	0.36	0.56
E	2.54	
F	1.27	
G	0.92	1.12
H	3.40	3.60

isc Silicon NPN Pow Transistor**2SC2229****ELECTRICAL CHARACTERISTICS****T_c=25°C unless otherwise specified**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _c = 10mA ; I _B = 1mA			0.5	V
V _{BE(sat)}	Base-Emitter Saturation Voltage	I _c = 10mA ; I _B = 1mA			1.0	V
I _{CB0}	Collector Cutoff Current	V _{CB} = 200V; I _E = 0			0.1	μ A
h _{FE}	DC Current Gain	I _c = 10mA ; V _{CE} = 5V	70		240	
f _T	Current-Gain—Bandwidth Product	I _c = 10mA ; V _{CE} = 30V		120		MHz
C _{OB}	Output Capacitance	I _E = 0 ; V _{CB} = 10V; f= 1.0MHz			5	pF